

General Description

The WSR30N65C series of devices use advanced trench gate super junction technology and design to provide excellent RDS(ON) with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

The WSR30N65C meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Green Device Available

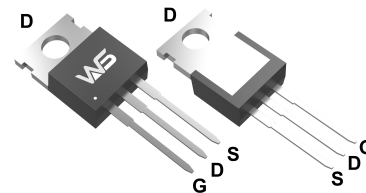
Product Summary

BV_{DSS}	R_{DSON}	I_D
650V	110m Ω	28A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter
- Networking DC-DC Power System
- Load Switch

TO-220F Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	650	V
V_{GS}	Gate-Source Voltage	± 30	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	28	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	18	A
I_{DM}	Pulsed Drain Current ²	112	A
EAS	Single Pulse Avalanche Energy ³	676	mJ
P_D	Total Power Dissipation ³	260	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	62.5	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	0.48	$^\circ C/W$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	650	---	---	V
ΔBV _{DSS} /ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.098	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =14A	---	110	140	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250μA	2.0	3.0	4.0	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-4.57	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =650V, V _{GS} =0V, T _J =25°C	---	---	1	μA
		V _{DS} =650V, V _{GS} =0V, T _J =125°C	---	---	100	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±200V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =9A	---	32	---	S
Q _g	Total Gate Charge (10V)	V _{DS} =100V, V _{GS} =10V, I _D =18A	---	38	---	nC
Q _{gs}	Gate-Source Charge		---	13	---	
Q _{gd}	Gate-Drain Charge		---	11.5	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =30V, V _{GS} =10V, R _G =6Ω, I _D =18A, R _L =30Ω	---	14	---	ns
T _r	Rise Time		---	12	---	
T _{d(off)}	Turn-Off Delay Time		---	65	---	
T _f	Fall Time		---	11	---	
C _{iss}	Input Capacitance	V _{DS} =30V, V _{GS} =0V, f=1MHz	---	2070	---	pF
C _{oss}	Output Capacitance		---	120	---	
C _{rss}	Reverse Transfer Capacitance		---	0.5	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,6}	V _G =V _D =0V, Force Current	---	---	28	A
I _{SM}	Pulsed Source Current ^{2,6}		---	---	112	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =28A, T _J =25°C	---	---	1.2	V
t _{rr}	Reverse Recovery Time	I _F =14A, dI/dt=100A/μs, T _J =25°C	---	190	---	nS
Q _{rr}	Reverse Recovery Charge		---	2000	---	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition: T_J=25°C, V_{DD}=50V, V_G=10V, L=0.5mH, R_G=25Ω

Typical Characteristics

Figure1. Safe operating area

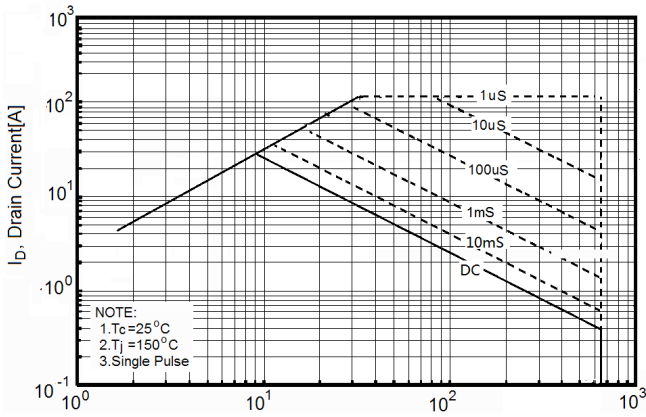


Figure2. Transient Thermal Impedance

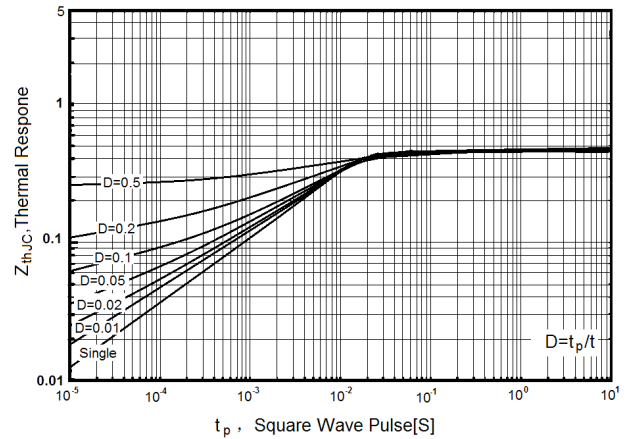


Figure3. Source-Drain Diode Forward Voltage

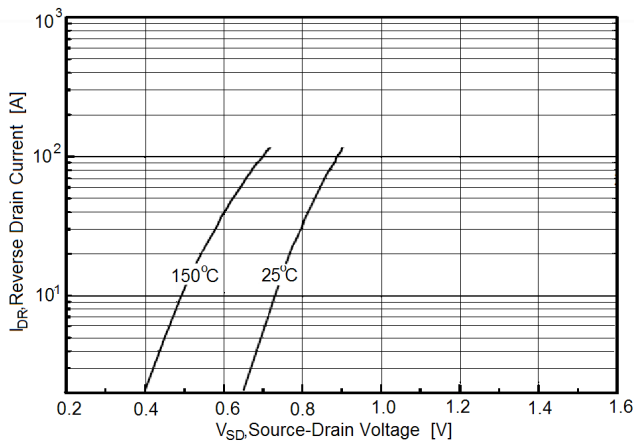


Figure4. Output characteristics

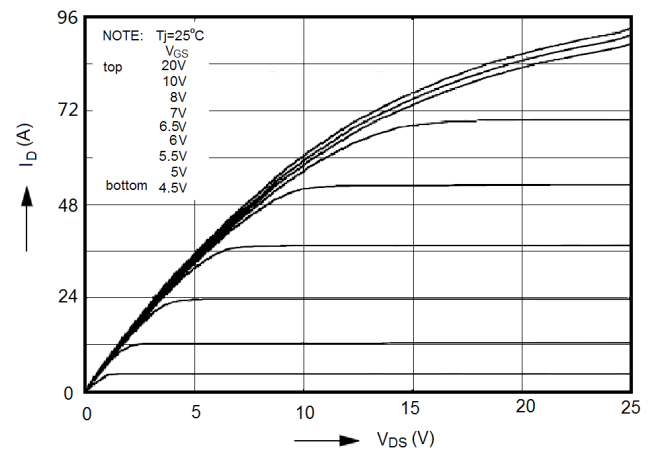


Figure5. Transfer characteristics

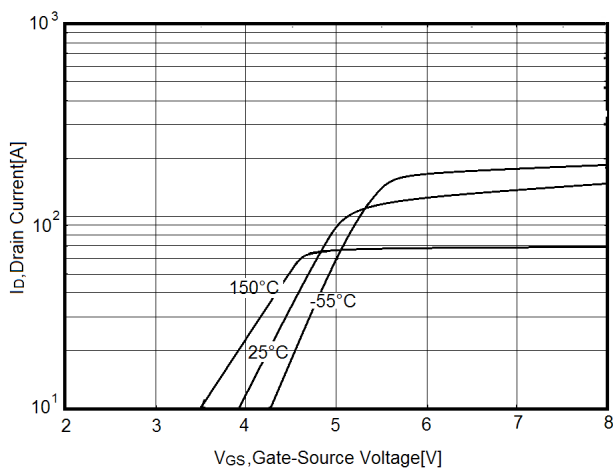


Figure6. Static drain-source on resistance

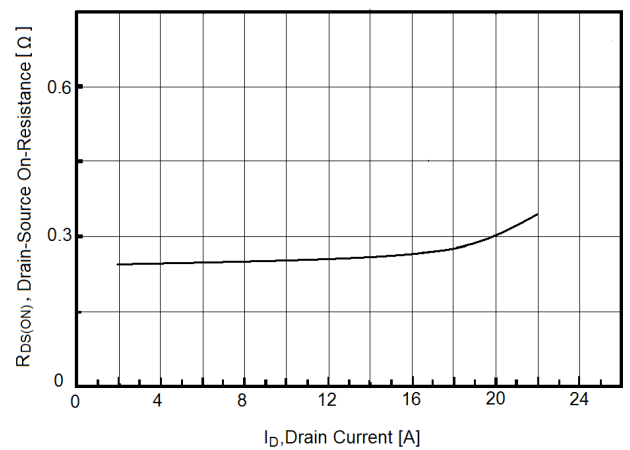


Figure7. $R_{DS(ON)}$ vs Junction Temperature

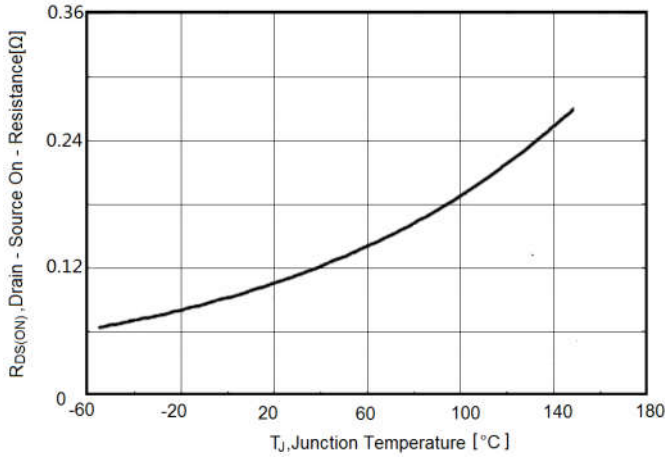


Figure8. BV_{DSS} vs Junction Temperature

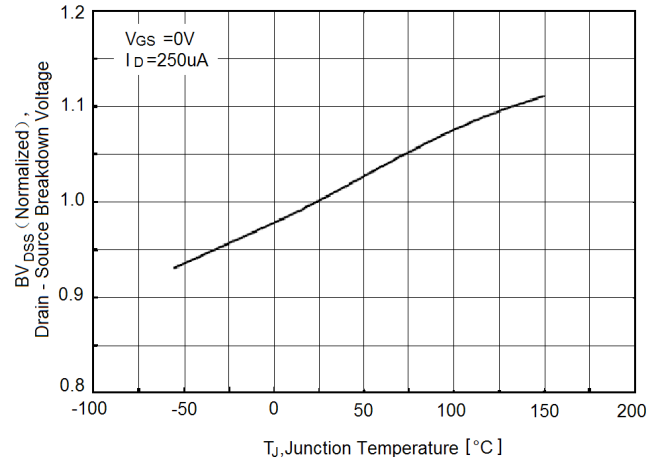


Figure9. Maximum I_D vs Junction Temperature

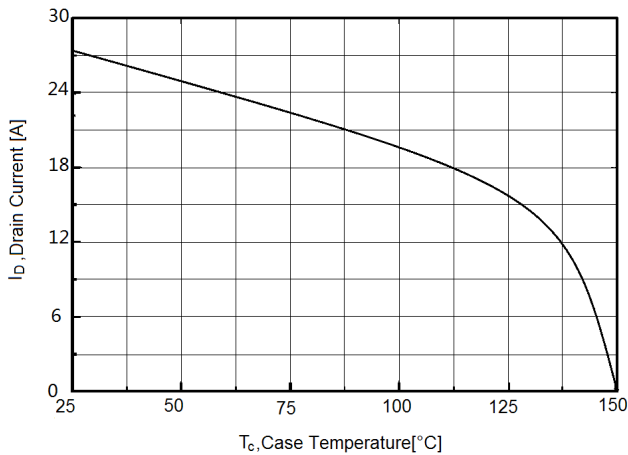


Figure10. Gate charge waveforms

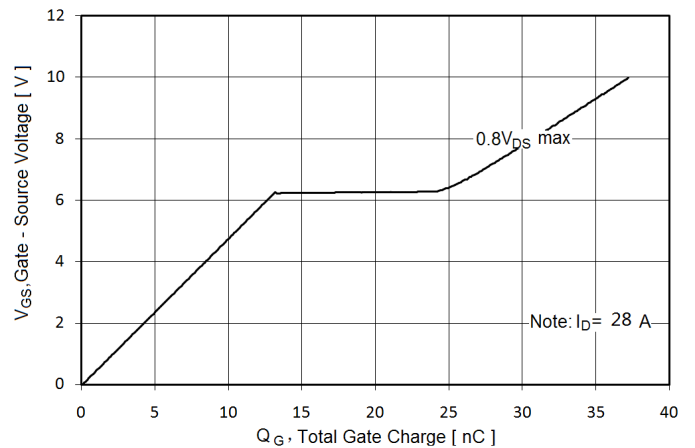
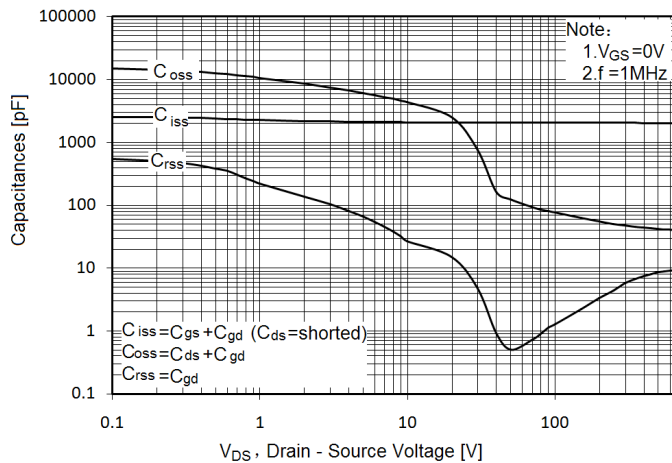
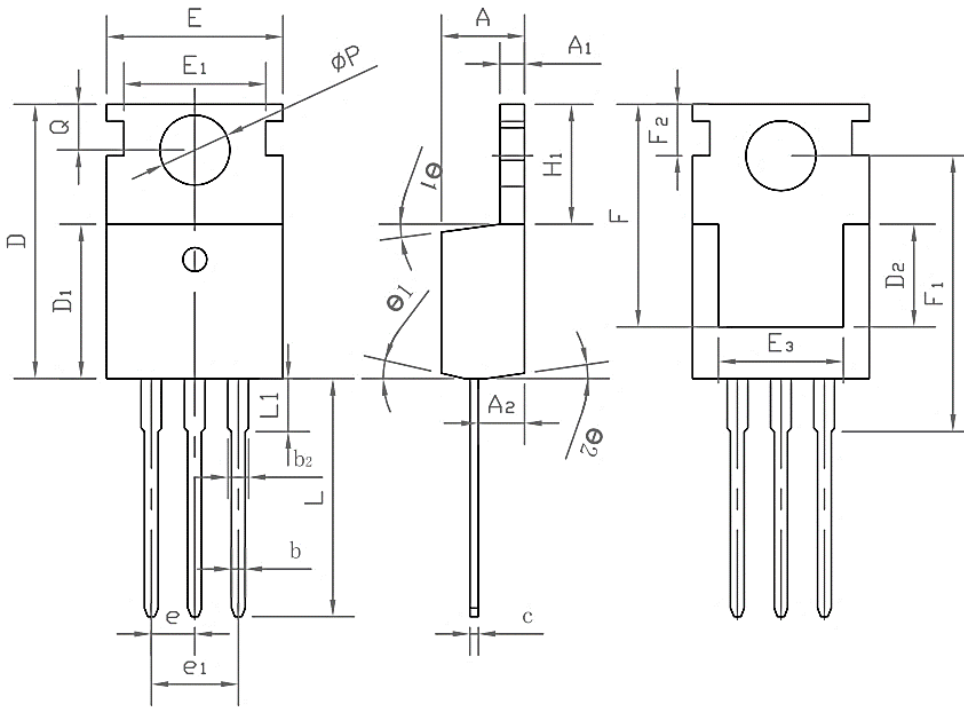


Figure11. Capacitance

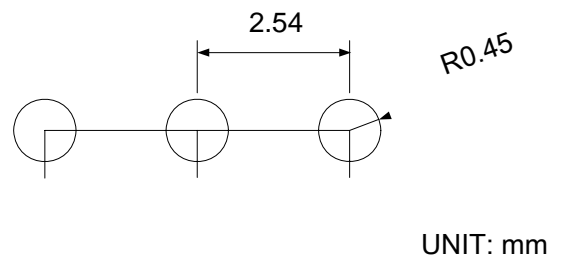


TO-220 Package Information



TO-220	TO-220			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.20	4.80	0.165	0.189
A1	2.34	3.20	0.092	0.126
A2	2.10	2.90	0.083	0.114
b	0.50	0.90	0.020	0.035
b2	0.91	1.90	0.035	0.075
c	0.30	0.80	0.012	0.031
D	8.10	9.40	0.319	0.370
d1	14.50	16.50	0.571	0.650
d2	12.10	12.90	0.476	0.508
E	9.70	10.70	0.382	0.421
e	2.54 BSC		0.100 BSC	
L	13.00	14.50	0.512	0.570
L1	1.60	4.00	0.063	0.157
P	3.00	3.60	0.118	0.142

RECOMMENDED LAND PATTERN





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